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# **Low-Temperature-Processed Thin-Film Transistors**

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## TABLE OF CONTENTS

<b>Pressure Dependence on the Electrical Properties of SiO<sub>2</sub> Gate Oxide Formed by Inductive Coupled Plasma Oxidation .....</b>	<b>1</b>
<i>Beom-Jong Kim, Dong-Chan Kim, Yoon-Jae Kim, Han-Jin Lim, Ju-Eun Kim, Wook-Yeol Yi, Dae-Hyun Kim, Bong-Hyun Kim, Young-Wan Kim, Sung-Ho Kang, Yung-Seok Kim, Woo-Jun Lee, Seok-Woo Nam, Chil-Hee Chung</i>	
<b>Low-damage Preparation of SiO<sub>2</sub> Dielectric Thin Film by the Photo-assisted Oxidation Processing .....</b>	<b>7</b>
<i>Takehito Kodzasa, Sei Uemura, Kouji Suemori, Manabu Yoshida, Satoshi Hoshino, Noriyuki Takada, Toshihide Kamata</i>	
<b>Effects of Oxygen and Forming Gas Annealing on ZnO TFTs .....</b>	<b>13</b>
<i>Jiaye Huang, Ujwal Radhakrishna, Martin Lemberger, Michael P. M. Jank, Sebastian Polster, Heiner Ryssel, Lothar Frey</i>	
<b>Low Temperature Zinc Indium Oxide Backplane Development for Flexible OLED Displays in a Manufacturing Pilot Line Environment .....</b>	<b>19</b>
<i>Michael A. Marrs, Sameer M. Venugopal, Curtis D. Moyer, Edward J. Bawolek, Dirk Bottesch, Barry P. O'Brien, Rita J. Cordova, Jovan Trujillo, Cynthia S. Bell, Douglas E. Loy, Gregory B. Raupp, David R. Allee</i>	
<b>Characteristics of OTFTs Using Olefin-polymer Gate Insulator and Their Application to a 5-in. OTFT-driven Flexible AMOLED Display .....</b>	<b>25</b>
<i>Yoshiki Nakajima, Yoshihide Fujisaki, Tatsuya Takei, Hiroto Sato, Mitsuru Nakata, Mitsunori Suzuki, Hirohiko Fukagawa, Genichi Motomura, Takahisa Shimizu, Koichi Sugitani, Yukie Isogai, Takeyoshi Katoh, Toshihiro Yamamoto, Hideo Fujikake, Shizuo Tokito</i>	
<b>Organic/Inorganic Hybrid-Type Nonvolatile Memory Thin-Film Transistor on Plastic Substrate below 150°C .....</b>	<b>31</b>
<i>Sung-Min Yoon, Shinhyuk Yang, Soon-Won Jung, Sang-Hee Ko Park, Chun-Won Byun, Min-Ki Ryu, Himchan Oh, Kyoungwan Kim, Chi-Sun Hwang, Kyoung-Ik Cho, Byoung-Gon Yu</i>	
<b>Precursor Design and Engineering for Low-temperature Deposition of Gate Dielectrics for Thin Film Transistors .....</b>	<b>36</b>
<i>Anupama Mallikarjunan, Laura M. Matz, Andrew D. Johnson, Raymond N. Vrtis, Manchao Xiao, Mark O. Neill, Bing Han</i>	
<b>Capacitance-Voltage Measurement of an Ambipolar Pentacene Field Effect Transistor in Operation by Using Displacement Current Measurement .....</b>	<b>45</b>
<i>Yuya Tanaka, Yutaka Noguchi, Hisao Ishii</i>	
<b>Development of ZnO/Ta<sub>2</sub>O<sub>5</sub> Heterojunction Using Low-temperature Technological Processes .....</b>	<b>51</b>
<i>R. Baca, J. A. Andraca, M. G. Arellano, G. R. Paredes, R. P. Sierra</i>	
<b>Spin-On Glass as Low Temperature Gate Insulator .....</b>	<b>57</b>
<i>Miguel A. Domínguez, Pedro Rosales, Alfonso Torres, Joel Molina, Mario Moreno, Francisco J. De La Hidalga, Carlos Zuñiga, Wilfrido Calleja</i>	

<b>Amorphous IGZO TFTs and Circuits on Highly Flexible and Dimensionally Stable Kovar (Ni-Fe alloy) Metal Foils .....</b>	<b>63</b>
<i>Shahrukh A. Khan, Xiaoxiao Ma, Nack Bong Choi, Miltiadis Hatalis</i>	
<b>Solution Processable Nanowire Field-Effect Transistors.....</b>	<b>69</b>
<i>Charles Opoku, Lichun Chen, Frank Meyer, Maxim Shkunov</i>	
<b>Millisecond-annealing Using Flash Lamps for Improved Performance of AZO Layers .....</b>	<b>75</b>
<i>T. Gebel, M. Neubert, R. Endler, J. Weber, M. Vinnichenko, A. Kolitsch, W. Skorupa, H. Liepack</i>	
<b>Author Index</b>	